

91 electrically insulated from the emitter contact to be formed in a subsequent stage of the production process.

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5. (amended) A method as claimed in claim 3, characterized in that during the etching operation, parts of the layer of electrically insulating material are protected against etching by a mask in the intermediate region at the location where this intermediate region adjoins the isolation region, so that said strips of electrically insulating material separating the emitter region from the isolation region are formed by etching.

92 6. (amended) A method as claimed in claim 1, characterized in that the doping step carried out to form the intrinsic base region is performed prior to the provision of said strips of electrically insulating material.

7. (amended) A method as claimed in claim 1, characterized in that, if use is made of a semiconductor body of silicon, the surface of the active region is covered at the location of the intermediate region with a masking layer to form said strips of electrically insulating material, which masking layer protects the surface against oxidation and can be selectively etched with respect to silicon oxide, and said masking layer leaves parts of